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03500.010530.4 PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	:	Examiner: G. Fourson, III
KIYOFUMI SAKAGUCHI, ET AL.	)	
	:	
Application No.: 09/161,774	)	Group Art Unit: 2823
	:	
Filed: September 29, 1998	)	
	:	
For: PROCESS FOR PRODUCTION OF SEMICONDUCTOR SUBSTRATE	) :	November 25, 2003

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

FOURTH INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449.

REMARKS

Applicants have cited U.S. Patent Nos. 5,811,348, 6,107,213, 6,194,245, 6,326,280, 6,426,274, and the documents cited therein. Applicants note that the claims of the subject application have been copied from the first listed patent, and that the remaining patents cross-reference that patent.

FORMAL MATTERS

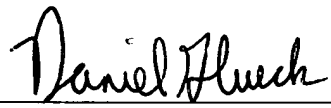
Any fee required in connection with this paper should be charged to Deposit Account 06-1205. A duplicate of this paper is enclosed.

CONCLUSION

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should be directed to our address given below.

Respectfully submitted,



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FORM PTO 1449 (*modified*)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT(S)
(*Use several sheets if necessary*)

Submitted: November 25, 2003

ATTY DOCKET NO.	APPLICATION NO.
03500.010530.4	09/161,774

APPLICANT: **KIYOFUMI SAKAGUCHI, ET AL.**

FILING DATE	GROUP
September 29, 1998	2823

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		4,116,751	09/26/78	Zaromb	156	600	
		4,727,047	02/23/88	Bozler, et al.	437	89	
		5,248,621	09/28/93	Sano	437	3	
		5,250,460	10/05/93	Yamagata, et al.	437	62	
		5,277,748	01/11/94	Sakaguchi, et al.	156	630	
		5,278,092	01/11/94	Sato	437	90	
		5,278,093	01/11/94	Yonehara	437	109	
		5,285,078	02/08/94	Mimura, et al.	257	3	
		5,290,712	03/01/94	Sato, et al.	437	24	
		5,320,907	06/14/94	Sato	428	446	
		5,331,180	07/19/94	Yamada, et al.	257	3	
		5,362,683	11/08/94	Takenaka, et al.	437	226	
		5,363,793	11/15/94	Sato	117	2	
		5,371,037	12/06/94	Yonehara	437	86	
		5,374,564	12/20/94	Bruel	437	24	
		5,403,771	04/04/95	Nishida, et al.	437	89	
		5,433,168	07/18/95	Yonehara	117	90	
		5,453,394	09/26/95	Yonehara, et al.	437	62	
		5,457,058	10/10/95	Yonehara	437	24	
		5,459,081	10/17/95	Kajita	437	3	
		5,466,631	11/14/95	Ichikawa, et al.	437	62	
		5,536,361	07/16/96	Kondo, et al.	156	630.1	

EXAMINER | DATE CONSIDERED

**EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.*

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LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)	APPLICANT KIYOFUMI SAKAGUCHI, ET AL.	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,644,156	07/01/97	Suzuki, et al.	257	485	
		5,670,411	09/23/97	Yonehara, et al.	437	62	
		5,811,348	09/22/98	Matsushita, et al.	438	455	
		5,854,123	12/29/98	Sato, et al.	438	507	
		5,856,229	01/05/99	Sakaguchi, et al.	438	406	
		5,863,830	01/26/99	Bruel, et al.	438	478	
		5,869,387	02/09/99	Sato, et al.	438	459	
		5,970,361	10/19/99	Kumomi, et al.	438	409	
		5,980,633	11/09/99	Yamagata, et al.	117	94	
		6,103,598	08/15/00	Yamagata, et al.	438	459	
		6,107,213	08/22/00	Tayanaka	438	762	
		6,121,117	09/19/00	Sato, et al.	438	459	
		6,194,245 B1	02/27/01	Tayanaka	438	57	
		6,326,280 B1	12/04/01	Tayanaka	438	409	
		6,426,274 B1	07/30/02	Tayanaka	438	458	

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	EP	√ 0417838 A1	03/20/91	EPO			
	EP	√ 0469630 A2	02/05/92	EPO			
	EP	0499488 A2	08/19/92	EPO			
	EP	0536790 A2	04/14/93	EPO			
	EP	0553852 A2	08/04/93	EPO			
	EP	√ 0553859 A3	08/04/93	EPO			

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	EP	0553860 A2	08/04/93	EPO			
	EP	0554795 A1	08/11/93	EPO			
	EP	0584777 A1	03/02/94	EPO			
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	EP	0757377 A2	02/05/97	EPO			
	EP	0793263 A2	09/03/97	EPO			
	EP	0797258 A2	09/24/97	EPO			
	GB	2211991 A	07/12/89	United Kingdom			
	JP	60-196955 V	10/05/85	Japan			Abstract
	JP	62-108539 V	05/19/87	Japan			Abstract
	JP	62-279625	12/04/87	Japan			Part Tran.
	JP	03-70156	03/26/91	Japan			Abstract
	JP	05-211128	08/20/93	Japan			Abstract
	JP	05-283722	10/29/93	Japan			Translation
	JP	06-45622	02/18/94	Japan			Translation
	JP	07-79016	03/20/95	Japan			Abstract
	JP	07-211602	08/11/95	Japan			Abstract
	JP	07-302889	11/14/95	Japan			Abstract
	JP	07-326719	12/12/95	Japan			Abstract

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JC	JP	9-162090	06/20/97	Japan			Abstract
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	√	H. Baumgart, et al., "Light Scattering Topography Characterization Of Bonded SOI Wafers", Extended Abstracts, Elect. Chem. Soc. 1st Symp., pp. 375-385 (1991)
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	√	Extended Abstracts (57th Autumn Meeting, 1996), The Japan Society of Applied Physics (Abstr. 8a-V-8) (with translation)
	√	Extended Abstracts (44th Spring Meeting, 1997), The Japan Society of Applied Physics and Related Societies (Abstr. 31a-B-5) (with translation)
	√	Extended Abstracts (59th Autumn Meeting, 1998), The Japan Society of Applied Physics (Abstr. 15a-YB-4) (with translation)
	√	C. Harendt et al., "Silicon on Insulator Material by Wafer Bonding," Journal of Electronic Materials, vol. 20, no. 3, pp. 267-277, March 1991.
	√	Y. Hashimoto, "Shin-Kagaku Yougo Jiten" (New Chemical Term Dictionary), Sankyo Shuppan Co., Ltd., 6th Edn (1973) (definition of anodic oxidation) (with translation)
	√	R.P. Holmstrom, et al. "Complete dielectric isolation by highly selective and self-stopping formation of oxidized porous silicon," Applied Physics Letters, vol. 42, no. 4, pp. 386-388, Feb. 1983.
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	√	K. Imai, "A New Dielectric Isolation Method Using Porous Silicon," Solid State Electronics, vol. 24, no. 2, pp. 159-164, 1981.
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	V	Patent Abstracts of Japan, vol. 18, No. 066 (E-1501), Feb. 3, 1994 (for JP-5-283722)
	V	V. Raineri, et al., "Silicon-on-insulator produced by helium implantation and thermal oxidation", Appl. Phys. Lett. 66(26), 3653-3656 (June 1995)
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